PNP general purpose Transistor

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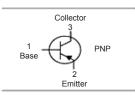


Features:

- Low current.(max.100mA)
- Low voltage.(max.65v)

Applications:

· General purpose switching and amplification





Maximum Ratings: @TA = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-80		
Collector-Emitter Voltage	V _{CEO}	-65	V	
Emitter-Base Voltage	V _{EBO}	-5		
Collector Current -Continuous	Ι _c	-0.1	A	
Collector Dissipation	P _c	250	mW	
Junction and Storage Temperature	T_{j},T_{stg}	-65 to 150	°C	

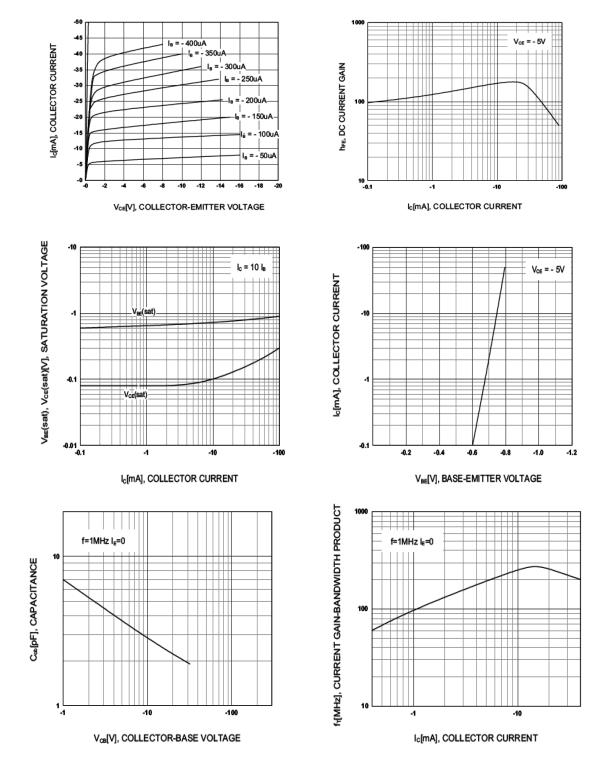
Electrical Characteristics: @TA = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT	
Collector-base breakdown voltage	V _{(BR)CBO}	$I_{c} = -10\mu A, I_{E} = 0$	-80	-	-		
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = -10mA, I _B = 0	-65	-	-	V	
Emitter-base breakdown voltage	V _{(BR)EBO}	Ι _E = -1μΑ, Ι _C = 0	-5	-	-		
Collector cut-off current	I _{сво}	$V_{CB} = -30V, I_{E} = 0$	-	-1	-15	nA	
Emitter cut-off current	I _{EBO}	$V_{EB} = -5V, I_{C} = 0$	-	-	-01	μA	
DC current gain	h _{FE}	V _{ce} = -5V, I _c = -2mA	125	-	250	-	
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{c} = -100$ mA, $I_{B} = -5$ mA $I_{c} = -10$ mA, $I_{B} = -0.5$ mA	-	-	-0.65 -0.3	V	
Base-emitter saturation voltage	$V_{BE(sat)}$	I _c = -100mA, I _B = -5mA	-	-	-1.1		
collector capacitance	C _c	$V_{CB} = -10V, I_{E} = I_{e} = 0$ f = 1MHz	-	4.5		pF	
Transition frequency	f _T	V _{ce} = -5V, I _c = -10mA f = 100MHz	100	-	-	MHz	

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Typical Characteristics @ TA = 25°C unless otherwise specified

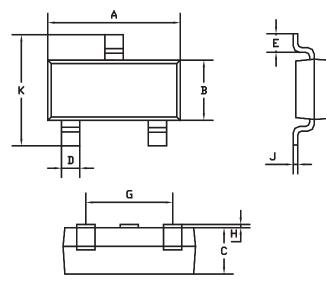
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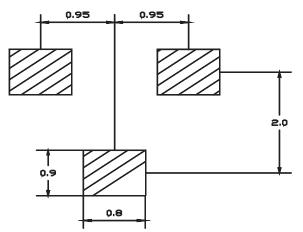
Package Outline:



SOT-23					
Dimension	Min	Мах			
А	2.85	2.95			
В	1.25	1.35			
С	1 Typical				
D	0.37	0.43			
Е	0.35	0.48			
G	1.85	1.95			
Н	0.02	0.1			
J	0.1 Typical				
K	2.35	2.45			

Dimensions : Millimetres

Soldering Footprint:



Dimensions : Millimetres

Part Number Table

Description	Part Number		
PNP general purpose Transistor	BC856A-7-F		

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